

< C band internally matched power GaAs FET >

MGFC45V4450A

4.4 - 5.0 GHz BAND / 32W

DESCRIPTION

The MGFC45V4450A is an internally impedance-matched GaAs power FET especially designed for use in 4.4 – 5.0 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation

Internally matched to 50(ohm) system

• High output power

P1dB=32W (TYP.) @f=4.4 - 5.0GHz

• High power gain

GLP=10.0dB (TYP.) @f=4.4 - 5.0GHz

High power added efficiency

P.A.E.=34% (TYP.) @f=4.4 - 5.0GHz

• Low distortion [item -51]

IM3=-45dBc (TYP.) @Po=34.5dBm S.C.L

APPLICATION

• item 01: 4.4 – 5.0 GHz band power amplifier

• item 51: 4.4 – 5.0 GHz band digital radio communication

QUALITY

• IG

RECOMMENDED BIAS CONDITIONS

• VDS=10V • ID=8.0A • RG=25ohm

Absolute maximum ratings (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain breakdown voltage	-15	V
VGSO	Gate to source breakdown voltage	-15	V
ID	Drain current	Α	
IGR	Reverse gate current	rse gate current -80	
IGF	Forward gate current	168	mA
PT *1	Total power dissipation	150	W
Tch	Cannel temperature	175	°C
Tstg	Storage temperature	-65 to +175	°C
Tstg	ŭ i	-65 to +175	°C

1 : Tc=25°C

unit:mm **OUTLINE** 24 +/- 0.3 R1.2 17.4 +/- 0.2 (2) 20.4 +/- 0.2 +/- 0.05 +/- 0.2 (1) gate (2) source(flange) (3)drain GF-38

Keep Safety first in your circuit designs! Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measure such as (I) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

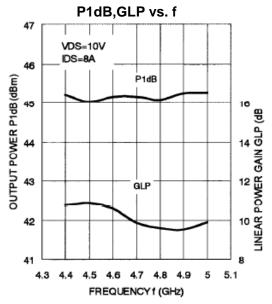
Electrical characteristics (Ta=25°C)

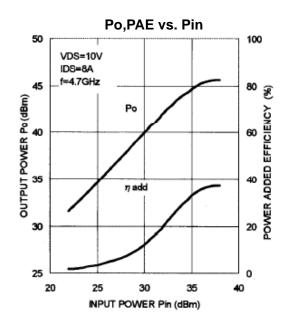
Symbol	Parameter	Test conditions	Limits		Unit	
			Min.	Тур.	Max.	
IDSS	Saturated drain current	VDS=3V,VGS=0V	-	24	-	Α
gm	Transconductance	VDS=3V,ID=8.0A	-	8	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V,ID=160mA	-2	-	-5	V
P1dB	Output power at 1dB gain compression	VDS=10V,ID(RF off)=8.0A	44	45	-	dBm
GLP	Linear Power Gain	f=4.4 - 5.0GHz	9	10	-	dB
ID	Drain current		-	8	-	А
P.A.E.	Power added efficiency		-	34	-	%
IM3 *2	3rd order IM distortion		-42	-45	-	dBc
Rth(ch-c) *3	Thermal resistance	delta Vf method	-	0.8	1	°C/W

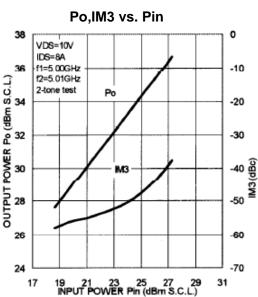
^{*2 :}item -51 ,2 tone test,Po=34.5dBm Single Carrier Level ,f=4.4,4.7,5.0GHz,delta f=10MHz

^{*3:} Channel-case

MGFC45V4450A TYPICAL CHARACTERISTICS (Ta=25deg.C)







$\textbf{MGFC45V4450A S-parameters}(\ \texttt{Ta=25deg.C}\ ,\ \texttt{VDS=10(V)}, \texttt{IDS=8.0(A)}\)$

f (GHz)	S Parameters(Typ.)							
	S11		S21		S12		S22	
	Magn.	Angle(deg.)	Magn.	Angle(deg.)	Magn.	Angle(deg.)	Magn.	Angle(deg.)
4.4	0.58	-132	2.881	54	0.04	2	0.30	-56
4.5	0.59	-163	2.936	31	0.04	-21	0.23	-82
4.6	0.58	171	2.865	8	0.05	-52	0.16	-125
4.7	0.59	151	2.782	-12	0.05	-67	0.18	-170
4.8	0.56	134	2.670	-32	0.05	-94	0.24	160
4.9	0.54	120	2.628	-51	0.05	-112	0.32	138
5.0	0.50	111	2.528	-70	0.06	-129	0.38	125

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